FEATURES

- Ultrafast recovery time
- Ultrasoft recovery
- Very low I_{RRM}

HEXFRED[®] Ultrafast Soft Recovery Diode, 8 A

- Guaranteed avalanche
- · Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION / APPLICATIONS

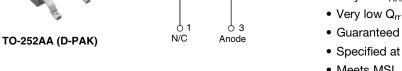
These diodes are optimized to reduce losses and EMI / RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Cathode to anode voltage	V _{RRM}		600	V						
Maximum continuous forward current	I _F	T _C = 100 °C	8							
Single pulse forward current	I _{FSM}		60	А						
Peak repetitive forward current	I _{FRM}		24							
Maximum power dissipation	PD	T _C = 100 °C	14	W						
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C						

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-				
Forward voltage	V _F	I _F = 8 A		-	1.4	1.7	V		
		I _F = 16 A	See fig. 1	-	1.7	2.1			
		I _F = 8 A, T _J = 125 °C		-	1.4	1.7			
Maximum reverse		$V_{R} = V_{R}$ rated	-	0.3	5.0				
leakage current	IR	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	100	500	μA			
Junction capacitance	CT	V _R = 200 V See fig. 3		-	10	25	pF		
Series inductance	L _S	Measured lead to lead 5 mm from pac	ckage body	-	8.0	-	nH		

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Q 2, 4

PRODUCT SUMMARY									
Package	TO-252AA (D-PAK)								
I _{F(AV)}	8 A								
V _R	600 V								
V _F at I _F	1.4 V								
t _{rr} typ.	18 ns								
T _J max.	150 °C								
Diode variation	Single die								

VS-HFA08SD60SPbF

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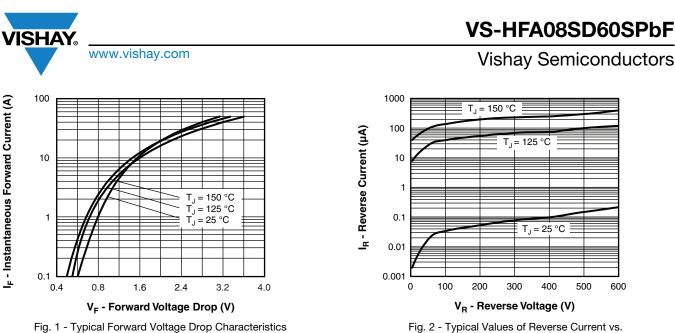


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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	-	18	-					
		T _J = 25 °C		-	37	55	ns			
		T _J = 125 °C	I _F = 8 A dI _F /dt = 200 A/µs V _R = 200 V	-	55	90				
Dook rooovory ourront	I _{RRM}	T _J = 25 °C		-	3.5	5.0	А			
Peak recovery current		T _J = 125 °C		-	4.5	8.0				
Poverse receivery charge	Q _{rr}	T _J = 25 °C		-	65	138	nC A/µs			
Reverse recovery charge		T _J = 125 °C		-	124	360				
Data of fall of recovery ourrent	dl _{(rec)M} /dt	T _J = 25 °C		-	240	-				
Rate of fall of recovery current		T _J = 125 °C		-	210	-				

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	ER SYMBOL TEST CONDITIONS					UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	150	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	3.5	°C/W			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	0/11			
Weight			-	2.0	-	g			
Weight			-	0.07	-	oz.			
Marking device		Case style D-PAK	HFA08SD60S						



Reverse Voltage

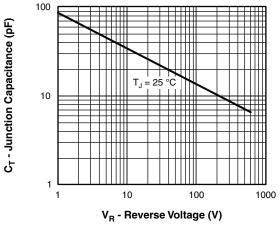


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

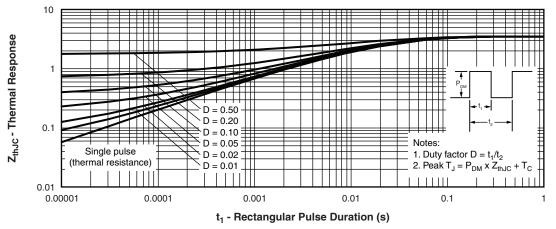


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



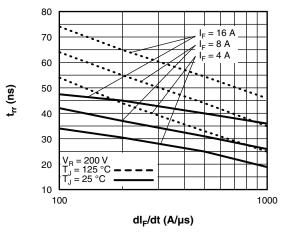


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

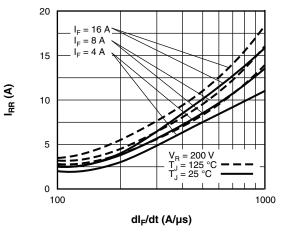
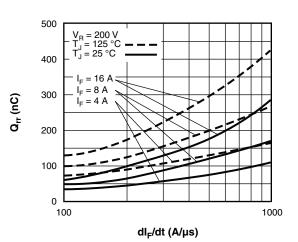
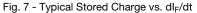


Fig. 6 - Typical Recovery Current vs. dl_F/dt

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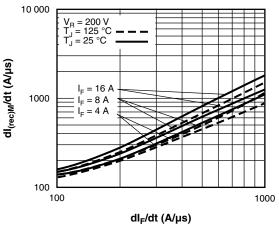


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

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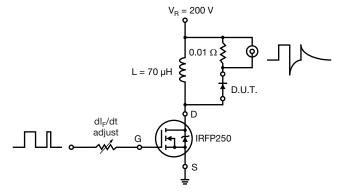
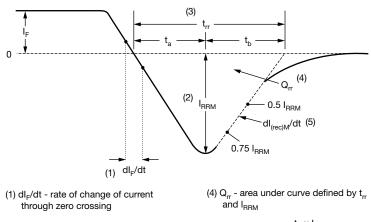


Fig. 9 - Reverse Recovery Parameter Test Circuit



(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.



(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

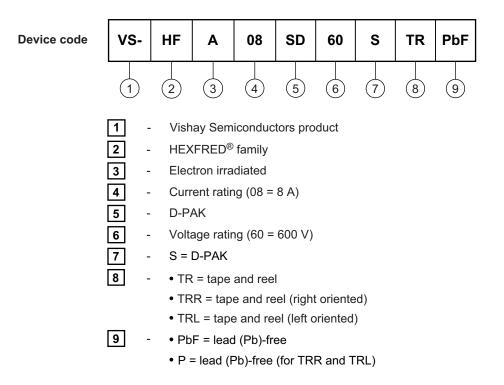
Fig. 10 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE



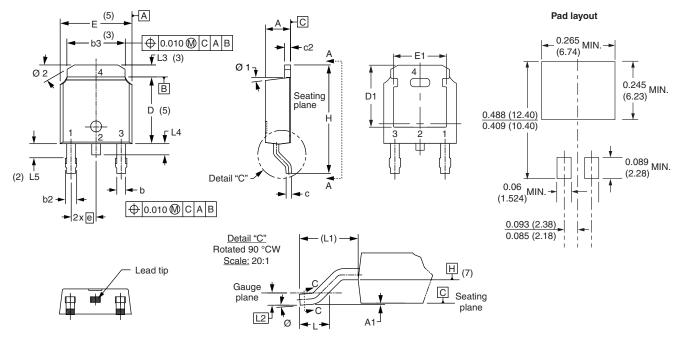
LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?95016							
Part marking information	www.vishay.com/doc?95059							
Packaging information	www.vishay.com/doc?95033							



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D-PAK (TO-252AA)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIDUL	MIN.	MAX.	MIN.	MAX.	NUTES
А	2.18	2.39	0.086	0.094			е	2.29	BSC	0.090) BSC	
A1	-	0.13	-	0.005			Н	9.40	10.41	0.370	0.410	
b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.070	
b2	0.76	1.14	0.030	0.045			L1	2.74	BSC	0.108	BREF.	
b3	4.95	5.46	0.195	0.215	3		L2	0.51	BSC	0.020	BSC	
с	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.050	3
c2	0.46	0.89	0.018	0.035			L4	-	1.02	-	0.040	
D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.060	2
D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°	
E	6.35	6.73	0.250	0.265	5		Ø1	0°	15°	0°	15°	
E1	4.32	-	0.170	-	3		Ø2	25°	35°	25°	35°	

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension uncontrolled in L5

⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

⁽⁴⁾ Section C - C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip

(5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁶⁾ Dimension b1 and c1 applied to base metal only

⁽⁷⁾ Datum A and B to be determined at datum plane H

⁽⁸⁾ Outline conforms to JEDEC outline TO-252AA

Document Number: 95016



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